

<b>SANYO</b>	No.4540	<b>3SK248</b>
		N-Channel Enhancement MOS Silicon FET Muting/Switching Applications

**Features**

- MOS FET with a back gate terminal.
- Enhancement type.
- Small ON resistance.
- Small-sized package permitting 3SK248-applied sets to be made smaller and slimmer.

**Absolute Maximum Ratings at Ta = 25°C**

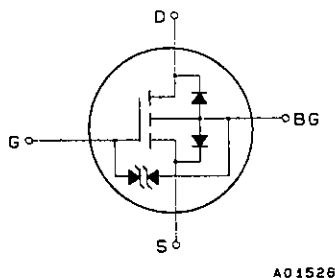
			unit
Drain-to-Source Voltage	$V_{DS}$	10	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 10$	V
Drain Current	$I_D$	100	mA
Allowable Power Dissipation	$P_D$	200	mW
Channel Temperature	$T_{ch}$	125	°C
Storage Temperature	$T_{stg}$	-55 to +125	°C

**Electrical Characteristics at Ta = 25°C**

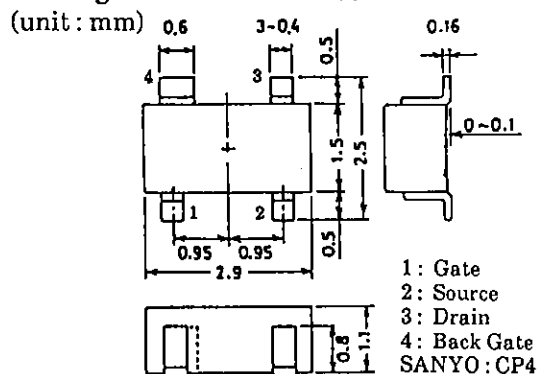
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10\mu A, V_{GS} = 0V$	10			V
G-S Breakdown Voltage	$V_{GSS}$	$I_G = \pm 10\mu A, V_{DS} = 0V$	$\pm 10$			V
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 8V, V_{DS} = 0V$		$\pm 0.01$	$\pm 50$	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 5V, I_D = 100\mu A$	0.3		1.5	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 5V, V_{GS} = 0V$			1	$\mu A$
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 5V, I_D = 50mA, f = 1kHz$		80		mS
Input Capacitance	$C_{iss}$	$V_{DS} = 5V, V_{GS} = 0V, f = 1MHz$		50		pF
Output Capacitance	$C_{oss}$	$V_{DS} = 5V, V_{GS} = 0V, f = 1MHz$		10		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = 5V, V_{GS} = 0V, f = 1MHz$		5		pF
Static Drain-to-Source on state Resistance	$R_{DS(on)1}$	$V_{GS} = 5V, I_D = 50mA$		5	7	$\Omega$
	$R_{DS(on)2}$	$V_{GS} = 2.5V, I_D = 15mA$		7	12	$\Omega$

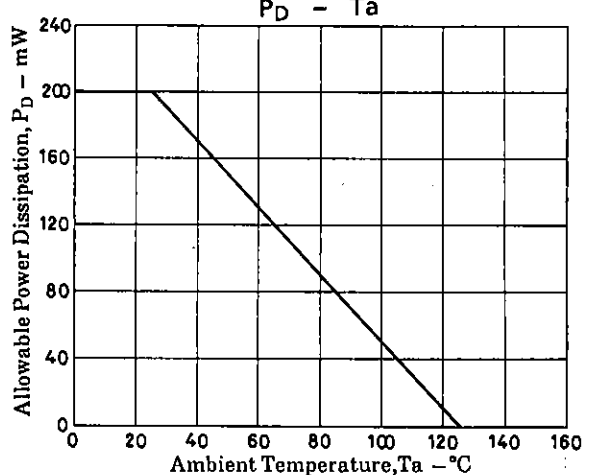
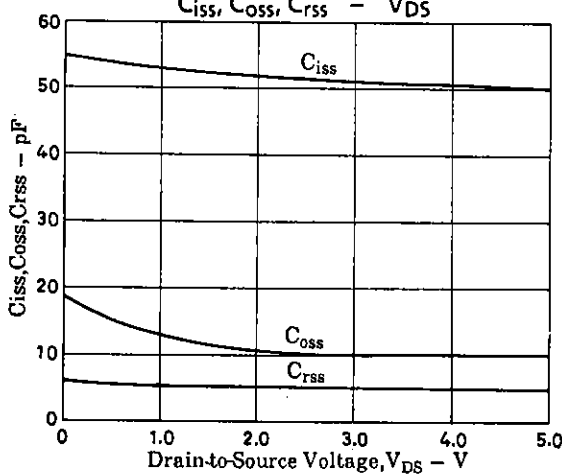
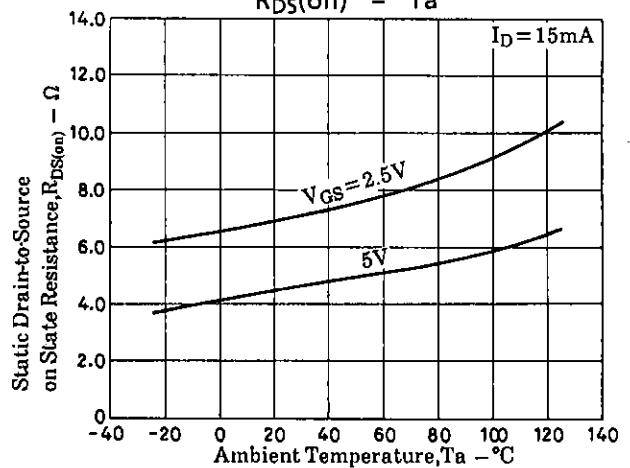
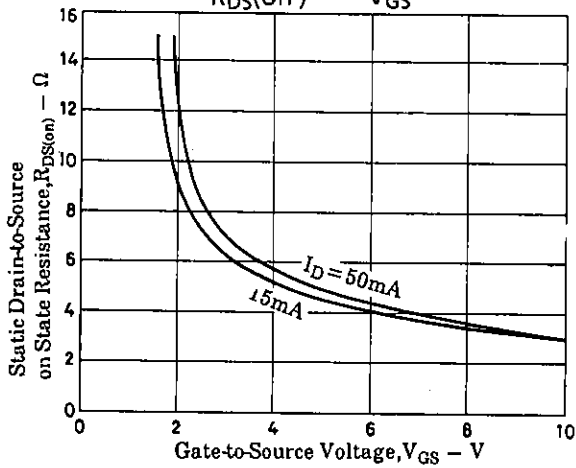
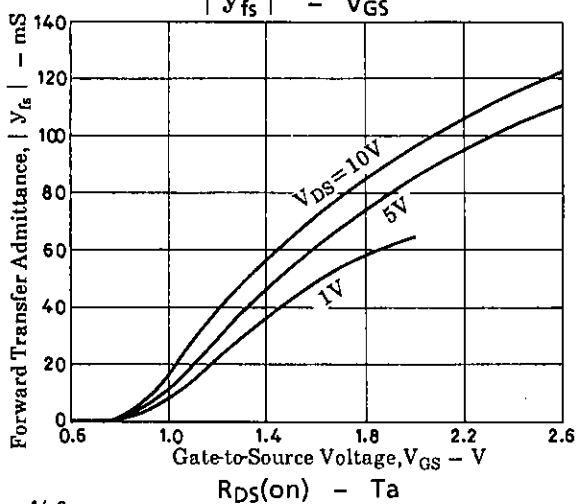
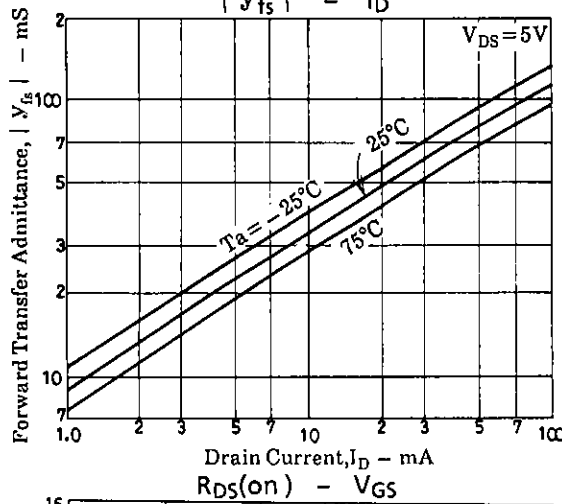
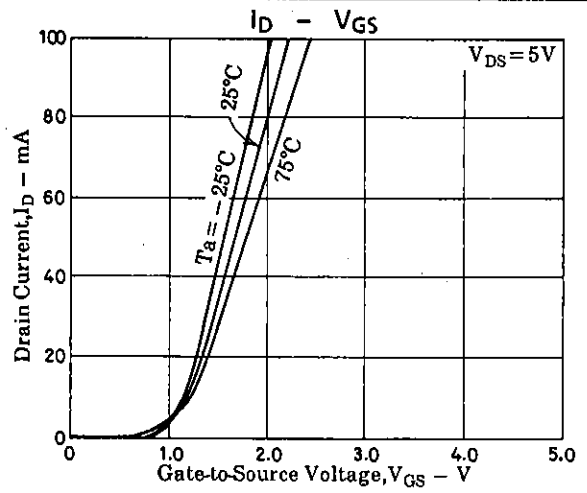
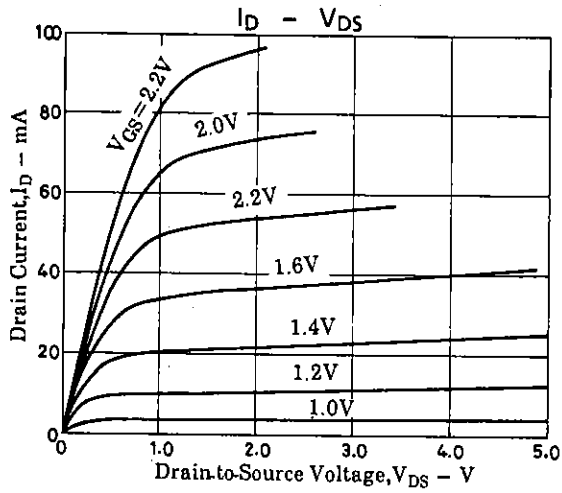
Marking : NJ

**Electrical Connection**



**Package Dimensions 2100A**





- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
  - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use;
  - ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.